

Rev.B Oct.-2020





SOT23-6 P MOS
P-channel MOSFET in a SOT23-6 Plastic Package

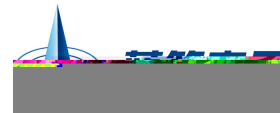
$V_{DS}(V) = -30V$
 $I_D = -4.2A (V_{GS} = -10V)$
 $R_{DS(ON)} < 50m\Omega (V_{GS} = -10V)$
 $R_{DS(ON)} < 65m\Omega (V_{GS} = -4.5V)$

This device is suitable for use as a load switch or in PWM applications.



PIN1 D PIN 2 D PIN 3 G PIN 4 S PIN 5 D PIN 6 D

See Marking Instructions

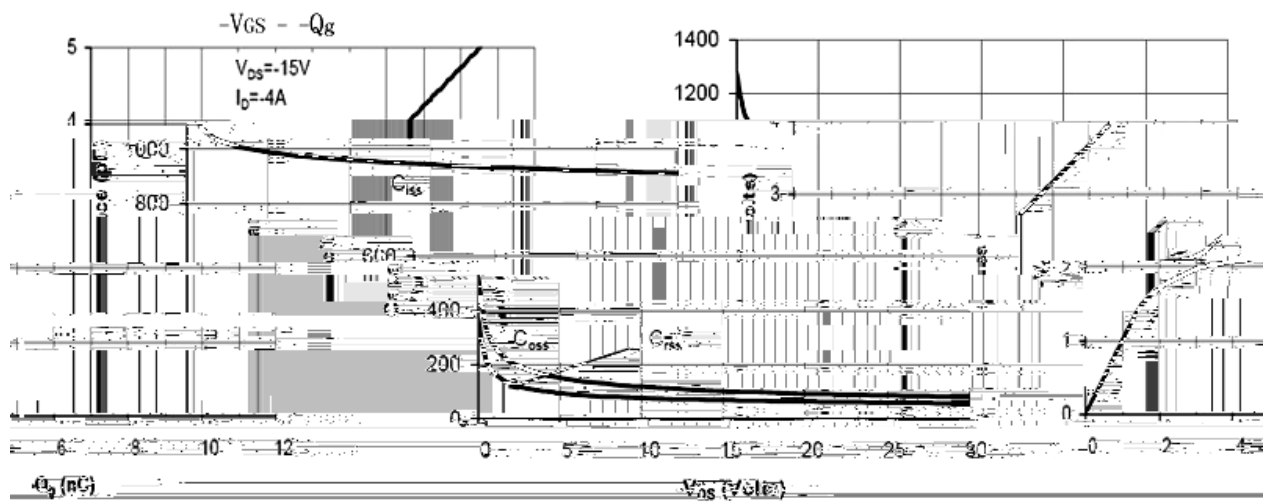


参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage	V_{DS}	-30	V
Drain Current – Continuous	$I_D(T_a=25^\circ\text{C})$	-4.2	A
Drain Current- Continuous ^A	$I_D(T_a=70^\circ\text{C})$	-3.5	A
Pulsed Drain Current ^B	I_{DM}	-30	A
Gate-Source Voltage	V_{GS}	± 12	V
Maximum Power Dissipation ^A	$P_D(T_a=25^\circ\text{C})$	1.4	W
Total Power Dissipation ^A	$P_D(T_a=70^\circ\text{C})$	1.0	W
Maximum Junction-to-Ambient ^(Note 1)	$R_{\theta JA}$	125	/ W
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	60	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	T_j, T_{stg}	-55 ~ 150	$^\circ\text{C}$

参数 符号
Parameter



Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Input Capacitance	C_{iss}	$V_{DS}=-15V$ $f=1MHz$ $V_{GS}=0V$		957		pF





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